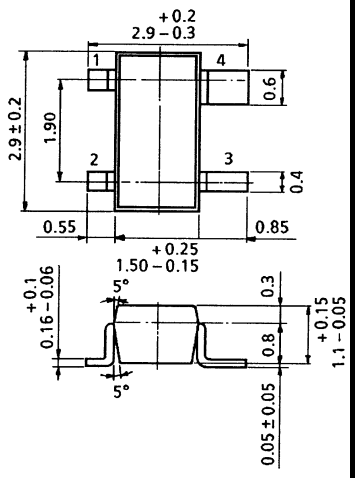
TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT4S06

VHF~UHF Band Low Noise Amplifier Applications

- Low noise figure: NF = 1.6dB (V_{CE} = 3 V, I_C = 3 mA, f = 2 GHz)
- High gain: $|S_{21e}|^2$ = 11.5dB (V_{CE} = 3 V, I_C = 7 mA, f = 2 GHz)

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-3J1C

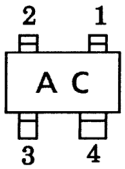
Weight: 0.012 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	10	V
Collector-emitter voltage	V_{CEO}	5	V
Emitter-base voltage	V_{EBO}	1.5	V
Base current	I_C	15	mA
Collector current	I_B	7	mA
Collector power dissipation	P_C	60	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking



Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Transition frequency	f_T	V_{CE} = 3 V, I_C = 5 mA	7	10	—	GHz
Insertion gain	$\|S_{21e}\|^2$ (1)	V_{CE} = 1 V, I_C = 5 mA, f = 2 GHz	—	10.5	—	dB
	$\|S_{21e}\|^2$ (2)	V_{CE} = 3 V, I_C = 7 mA, f = 2 GHz	8.5	11.5	—	
Noise figure	NF (1)	V_{CE} = 1 V, I_C = 3 mA, f = 2 GHz	—	1.7	3	dB
	NF (2)	V_{CE} = 3 V, I_C = 3 mA, f = 2 GHz	—	1.6	3	

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 5 V, I_E = 0	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 1 V, I_C = 0	—	—	1	μA
DC current gain	h_{FE}	V_{CE} = 1 V, I_C = 5 mA	70	—	140	
Reverse transfer capacitance	C_{re}	V_{CB} = 1 V, I_E = 0, f = 1 MHz (Note)	—	0.23	0.7	pF

Note: C_{re} is measured by 3 terminal method with capacitance bridge.

Caution

This device is sensitive to electrostatic discharge. Please handle with caution.

RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
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